

Title (en)

MEMORY AND METHOD FOR AN IMPROVED SENSING

Title (de)

HALBLEITERSPEICHER MIT VERBESSERTER LESEANORDNUNG SOWIE ZUGEHÖRIGE BETRIEBSART

Title (fr)

MEMOIRE A SEMI-CONDUCTEUR AVEC ENSEMBLE DE LECTURE AMELIORE, ET SON MODE DE FONCTIONNEMENT

Publication

EP 1412949 A1 20040428 (DE)

Application

EP 02754426 A 20020724

Priority

- DE 0202715 W 20020724
- DE 10137120 A 20010730

Abstract (en)

[origin: WO03015103A1] A selection transistor (2) for a group of memory cells, preferably 16-32 memory cells, is respectively introduced into the feed lines to the memory cells (4) The selection transistor is opened to a line group for reading, while the control gates of all lines are low potential and the current for each reading column leading through said line group is measured and stored. In a second step, the control gate (5) of the line to be read is brought to a higher reading potential and the resulting current is compared to the previous current.

IPC 1-7

G11C 16/26; **G11C 7/14**

IPC 8 full level

G11C 16/06 (2006.01); **G11C 16/26** (2006.01)

CPC (source: EP US)

G11C 16/26 (2013.01 - EP US)

Citation (search report)

See references of WO 03015103A1

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR IE IT LI LU MC NL PT SE SK TR

DOCDB simple family (publication)

WO 03015103 A1 20030220; CN 1537311 A 20041013; DE 10137120 A1 20030220; DE 10137120 B4 20090219; EP 1412949 A1 20040428; JP 2004538597 A 20041224; JP 2006351201 A 20061228; US 2004218417 A1 20041104; US 6940755 B2 20050906

DOCDB simple family (application)

DE 0202715 W 20020724; CN 02815093 A 20020724; DE 10137120 A 20010730; EP 02754426 A 20020724; JP 2003519944 A 20020724; JP 2006271292 A 20061002; US 76898804 A 20040130